

Silicon NPN Power Transistors

2SC3256

DESCRIPTION

- With TO-3PN package
- Fast switching speed
- Low saturation voltage

APPLICATIONS

- 60V/15A High-Speed Switching Applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

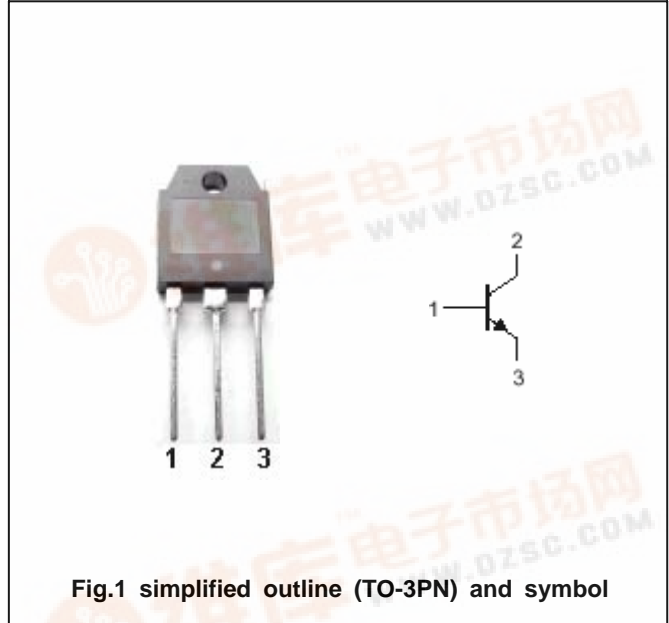


Fig.1 simplified outline (TO-3PN) and symbol

ABSOLUTE MAXIMUM RATINGS(T_C=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	80	V
V _{CEO}	Collector-emitter voltage	Open base	60	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		15	A
I _{CP}	Collector current-peak		20	A
P _C	Collector power dissipation	T _C =25°C	80	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

Silicon NPN Power Transistors

2SC3256

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =1mA ; R _{BE} =∞	60			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	80			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	5			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =7.5A ; I _B =0.375A			0.4	V
I _{CBO}	Collector cut-off current	V _{CB} =40V ; I _E =0			100	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =4V ; I _C =0			100	μ A
h _{FE}	DC current gain	I _C =1A ; V _{CE} =2V	70		280	
f _T	Transition frequency	I _C =1A ; V _{CE} =5V		100		MHz

Switching times

t _{on}	Turn-on time	I _C =6A ; I _{B1} =0.3A ; I _{B2} =-0.3A V _{CC} =20V		0.1		μ s
t _s	Storage time			0.5		μ s
t _f	Fall time			0.1		μ s

◆ h_{FE} Classifications

Q	R	S
70-140	100-200	140-280

Silicon NPN Power Transistors

2SC3256

PACKAGE OUTLINE

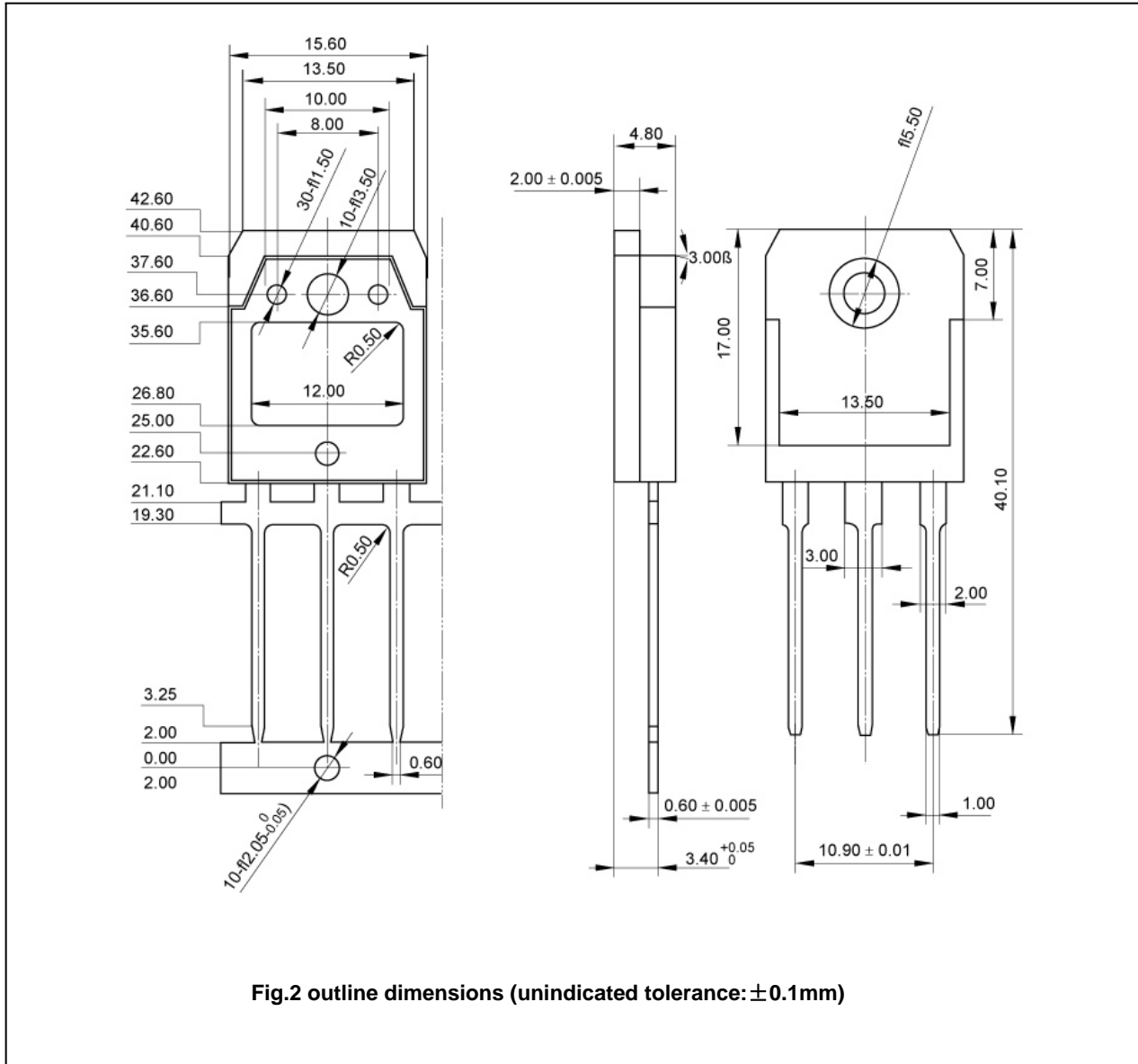


Fig.2 outline dimensions (unindicated tolerance: \pm 0.1mm)